

Title (en)

Method of increasing the layout efficiency of dies on a wafer, and increasing the ratio of I/O area to active area per die.

Title (de)

Verfahren zur Erhöhung der Lay out Effizienz von Elementen auf einer Scheibe und Erhöhung des Verhältnisses der E/A Fläche zur aktiven Fläche pro Element.

Title (fr)

Procédé pour augmenter l'efficacité de l'arrangement des puces sur une tranche et pour augmenter le rapport entre la surface I/O et la surface active d'une puce.

Publication

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Application

EP 93111442 A 19930716

Priority

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Abstract (en)

Certain non-square dies, such as triangular dies (e.g. 202a, 202b,...), greatly elongated rectangular dies, parallelogram dies, trapezoidal, and the like, are able to be laid out in the area of a circular semiconductor wafer (204) more "efficiently" than square dies. Further, a peripheral area of these certain non-square dies is advantageously increased relative to the area contained within the peripheral area, to accommodate increased I/O connections to the active elements of the die (202a, 202b,...). <IMAGE>

IPC 1-7

H01L 21/78; **H01L 27/02**

IPC 8 full level

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CPC (source: EP US)

G03F 7/70433 (2013.01 - EP US); **G06F 30/392** (2020.01 - EP US); **H01L 23/315** (2013.01 - EP US); **H01L 23/49503** (2013.01 - EP US); **H01L 23/49558** (2013.01 - EP US); **H01L 24/05** (2013.01 - EP US); **H01L 24/06** (2013.01 - EP US); **H01L 24/48** (2013.01 - EP US); **H01L 24/49** (2013.01 - EP US); **H01L 27/0207** (2013.01 - EP US); **H01L 29/0657** (2013.01 - EP US); **H01L 24/45** (2013.01 - EP US); **H01L 2224/0401** (2013.01 - EP US); **H01L 2224/04042** (2013.01 - EP US); **H01L 2224/05552** (2013.01 - EP US); **H01L 2224/05554** (2013.01 - EP US); **H01L 2224/05555** (2013.01 - EP US); **H01L 2224/05599** (2013.01 - EP US); **H01L 2224/16145** (2013.01 - EP US); **H01L 2224/45144** (2013.01 - EP US); **H01L 2224/48091** (2013.01 - EP US); **H01L 2224/48455** (2013.01 - EP US); **H01L 2224/4847** (2013.01 - EP US); **H01L 2224/48599** (2013.01 - EP US); **H01L 2224/49109** (2013.01 - EP US); **H01L 2224/4912** (2013.01 - EP US); **H01L 2224/49171** (2013.01 - EP US); **H01L 2224/49173** (2013.01 - EP US); **H01L 2924/00014** (2013.01 - EP US); **H01L 2924/01005** (2013.01 - EP US); **H01L 2924/01006** (2013.01 - EP US); **H01L 2924/01013** (2013.01 - EP US); **H01L 2924/01014** (2013.01 - EP US); **H01L 2924/01015** (2013.01 - EP US); **H01L 2924/01027** (2013.01 - EP US); **H01L 2924/01039** (2013.01 - EP US); **H01L 2924/01074** (2013.01 - EP US); **H01L 2924/01075** (2013.01 - EP US); **H01L 2924/01079** (2013.01 - EP US); **H01L 2924/10155** (2013.01 - EP US); **H01L 2924/10253** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/15312** (2013.01 - EP US); **H01L 2924/1532** (2013.01 - EP US); **H01L 2924/15787** (2013.01 - EP US); **H01L 2924/181** (2013.01 - EP US); **H01L 2924/19041** (2013.01 - EP US); **H01L 2924/30105** (2013.01 - EP US); **H01L 2924/30111** (2013.01 - EP US); **Y10S 148/028** (2013.01 - EP US)

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